NSN 5961-01-465-5108

Diode Semiconductor Device - Page 1 of 1

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Inclosure Material:

Glass

End Application:

6625-01-391-2969

Mounting Facility Quantity:

2

Mounting Method:

Press fit

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

56.0 forward gate to source breakdown voltage and 1.8 forward gate to source breakdown voltage

Current Rating Per Characteristic:

1.50 nanoamperes forward current, average peak

Power Rating Per Characteristic:

500.0 milliwatts small-signal output power, common-base preset

Maximum Operating Tempurature Per Measurement Point:

-65.0 degrees celsius case and 200.0 degrees celsius case

Special Features:

Hermeticallysealed

Terminal Type And Quantity:

2 case

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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